



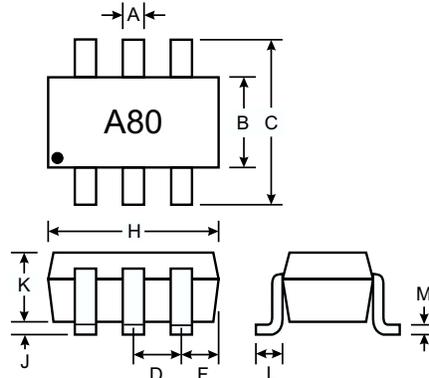
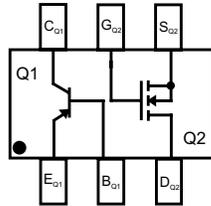
NEW PRODUCT

Features

- Combines MMBT4403 type transistor with 2N7002 type MOSFET
- Small Surface Mount Package
- NPN/P-Channel Complement Available: CTA2N1P

Mechanical Data

- Case: SOT-363, Molded Plastic
Terminals: Solderable per MIL-STD-202, Method 208
- Case material - UL Flammability Rating Classification 94V-0
- Terminal Connections: See Diagram
- Marking: A80
- Weight: 0.006 grams (approx.)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
All Dimensions in mm		

Maximum Ratings, Total Device @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	P _d	150	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	833	°C/W
Operating and Storage and Temperature Range	T _j , T _{STG}	-55 to +150	°C

Maximum Ratings, Q1, MMBT4403 PNP Transistor Element @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous	I _C	-600	mA

Maximum Ratings, Q2, 2N7002 N-Channel MOSFET Element @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	60	V
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ	V _{DGR}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
		±40	
Drain Current (Note 1)	I _D	115	mA
		73	
		800	

Electrical Characteristics, Q1, MMBT4403 PNP Transistor Element@ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-40	—	V	I _C = -100μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-40	—	V	I _C = -1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0	—	V	I _E = -100μA, I _C = 0
Collector Cutoff Current	I _{CEX}	—	-100	nA	V _{CE} = -35V, V _{EB(OFF)} = -0.4V
Base Cutoff Current	I _{BL}	—	-100	nA	V _{CE} = -35V, V _{EB(OFF)} = -0.4V
ON CHARACTERISTICS (Note 2)					
DC Current Gain	h _{FE}	30 60 100 100 20	— — — 300 —	—	I _C = -100μA, V _{CE} = -1.0V I _C = -1.0mA, V _{CE} = -1.0V I _C = -10mA, V _{CE} = -1.0V I _C = -150mA, V _{CE} = -2.0V I _C = -500mA, V _{CE} = -2.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	-0.40 -0.75	V	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	-0.75 —	-0.95 -1.30	V	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{cb}	—	8.5	pF	V _{CB} = -10V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{eb}	—	30	pF	V _{EB} = -0.5V, f = 1.0MHz, I _C = 0
Input Impedance	h _{ie}	1.5	15	kΩ	V _{CE} = -10V, I _C = -1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h _{re}	0.1	8.0	x 10 ⁻⁴	
Small Signal Current Gain	h _{fe}	60	500	—	
Output Admittance	h _{oe}	1.0	100	μS	
Current Gain-Bandwidth Product	f _T	200	—	MHz	V _{CE} = -10V, I _C = -20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	15	ns	V _{CC} = -30V, I _C = -150mA, V _{BE(off)} = -2.0V, I _{B1} = -15mA
Rise Time	t _r	—	20	ns	
Storage Time	t _s	—	225	ns	V _{CC} = -30V, I _C = -150mA, I _{B1} = I _{B2} = -15mA
Fall Time	t _f	—	30	ns	

Electrical Characteristics, Q2, 2N7002 N-Channel MOSFET Element@ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	70	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0 500	μA	V _{DS} = 60V, V _{GS} = 0V @ T _C = 25°C @ T _C = 125°C
Gate-Body Leakage	I _{GSS}	—	—	±10	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	V _{GS(th)}	1.0	—	2.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	3.2 4.4	7.5 13.5	Ω	V _{GS} = 5.0V, I _D = 0.05A V _{GS} = 10V, I _D = 0.5A @ T _J = 25°C @ T _J = 125°C
On-State Drain Current	I _{D(ON)}	0.5	1.0	—	A	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance	g _{FS}	80	—	—	mS	V _{DS} = 10V, I _D = 0.2A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	22	50	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	11	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	2.0	5.0	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	7.0	20	ns	V _{DD} = 30V, I _D = 0.2A, R _L = 150Ω, V _{GEN} = 10V, R _{GEN} = 25Ω
Turn-Off Delay Time	t _{D(OFF)}	—	11	20	ns	

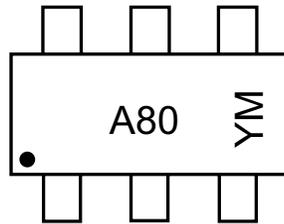
Note: 1. Device mounted on FR-4 PCB; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Ordering Information (Note 3)

Device	Packaging	Shipping
CTA2P1N-7	SOT-363	3000/Tape & Reel

Notes: 3. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004
Code	J	K	L	M	N	O	P

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

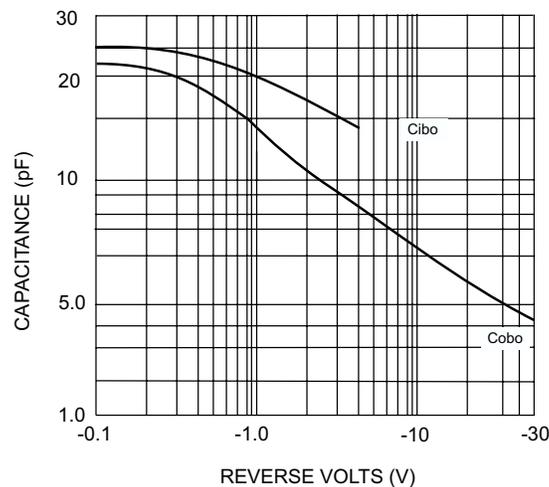


Fig. 1 Typical Capacitance (MMBT4403)

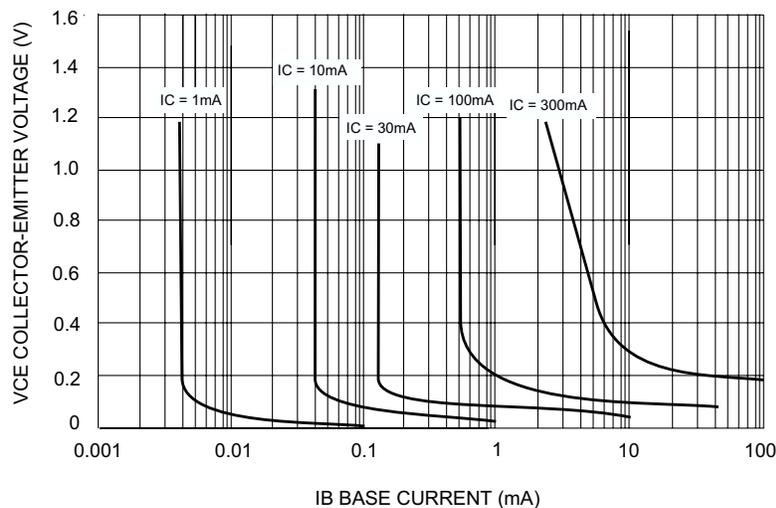


Fig. 2 Typical Collector Saturation Region (MMBT4403)

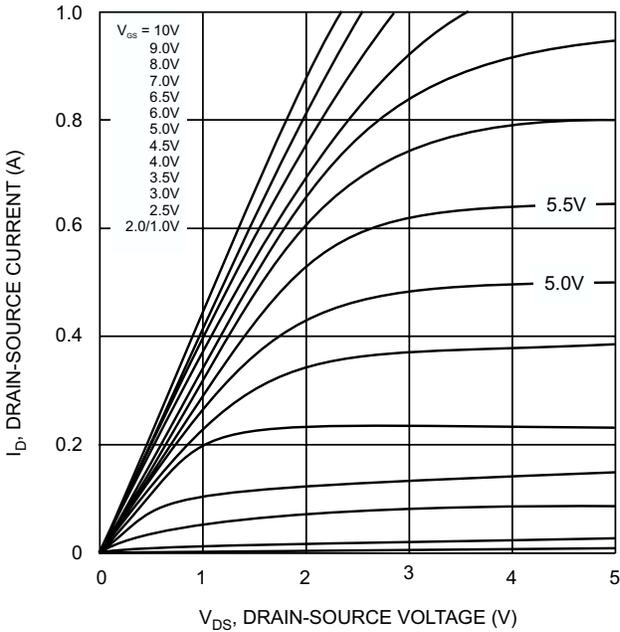


Fig. 3 On-Region Characteristics (2N7002)

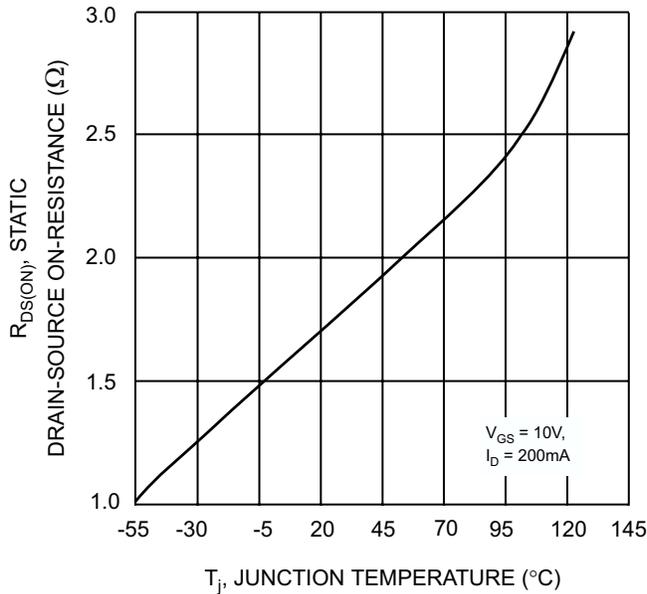


Fig. 5 On-Resistance vs Junction Temperature (2N7002)

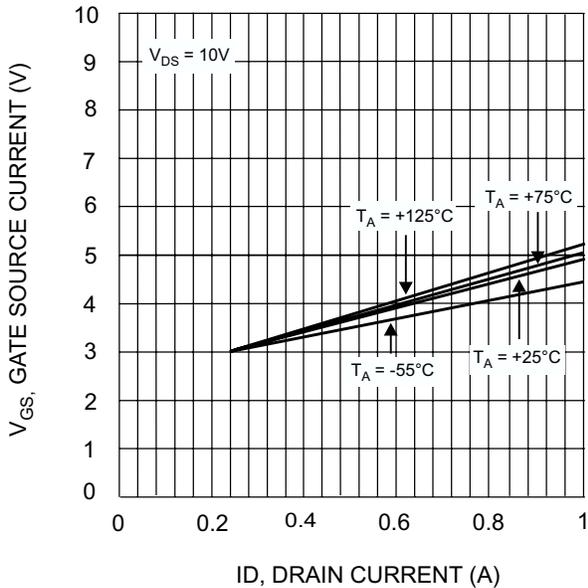


Fig. 7 Typical Transfer Characteristics (2N7002)

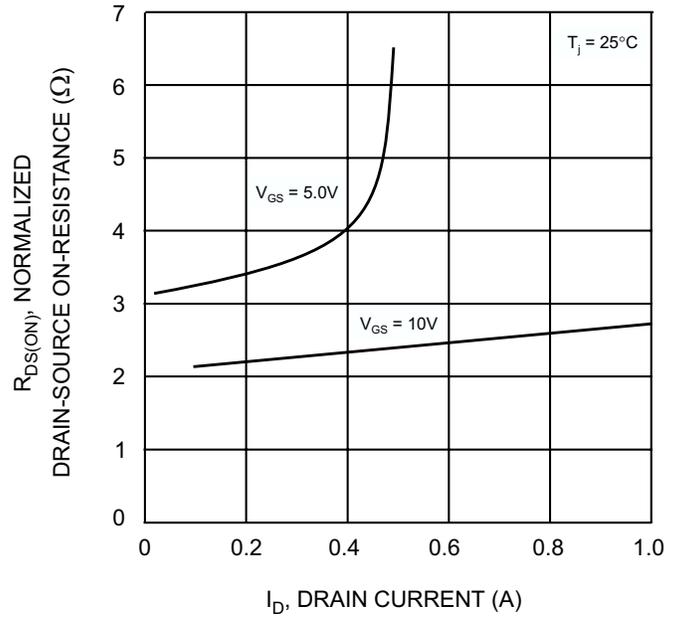


Fig. 4 On-Resistance vs Drain Current (2N7002)

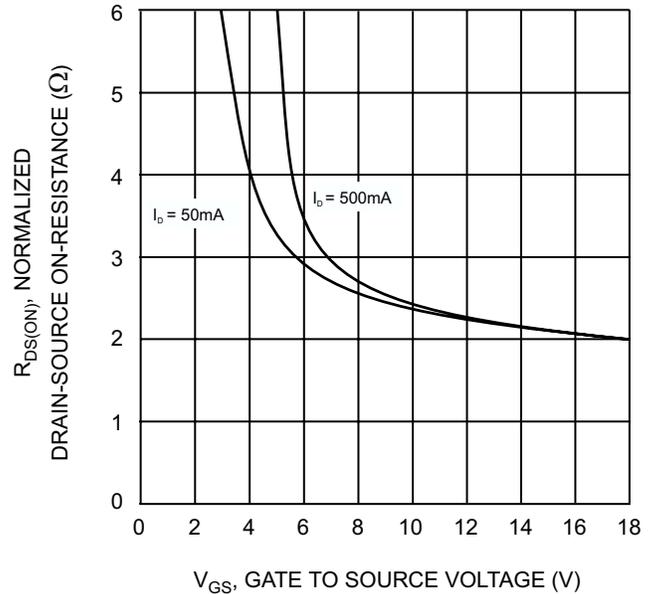


Fig. 6 On-Resistance vs. Gate-Source Voltage (2N7002)